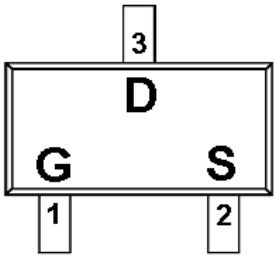
SPP1073
P-Channel Enhancement Mode MOSFET

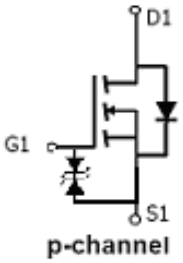
DESCRIPTION
The SPP1073 is t he P-Channel enhancement m ode power field effect transistors are produced using high cell density , D MOS trench technolog y. This high densit y process is especi ally tailored to minim ize on-state resistance an d provi de superior switching perform ance. These devic es are particu larly suited for low voltage applications such as noteboo k co mputer power management and other battery powered circuits where high-side s witching , low in-line power los s, and resistance to transients are needed.

APPLICATIONS
- Drivers : Relays/Solenoids/Lamps/Hammers
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

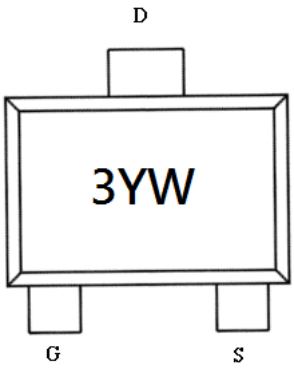
FEATURES
- P-Channel
  -20V/0.45A,$R_{DS(ON)}$= 0.65Ω@V_{GS}=-4.5V
  -20V/0.35A,$R_{DS(ON)}$= 0.90Ω@V_{GS}=-2.5V
  -20V/0.25A,$R_{DS(ON)}$= 1.5Ω@V_{GS}=-1.8V
- Super high density cell design for extremely low RDS (ON)
- Exceptional on-resistance and maximum DC current capability
- SOT-723 package design

PIN CONFIGURATION(SOT-723)





PART MARKING



SPP1073
P-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin Symbol		Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP1073S72RGB	SOT-723	3

※ SPP1073S72RGB : Tape Reel ; Pb – Free, Halogen – Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

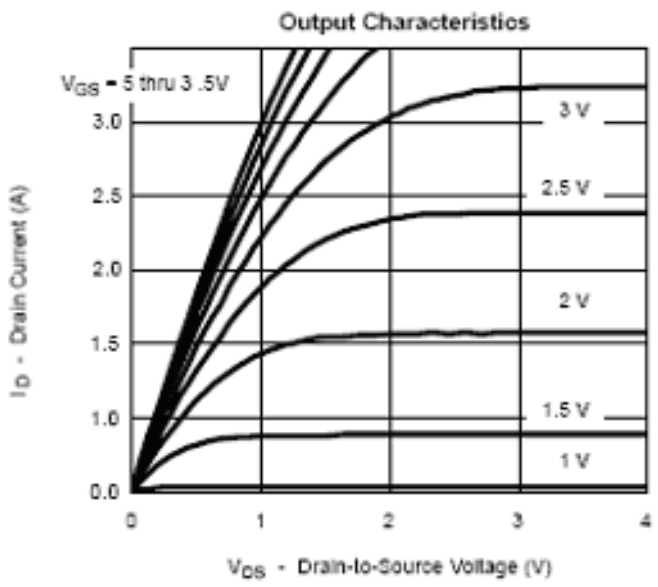
Parameter Symbol			Typical	Unit
Drain-Source Voltage		V_{DSS}	-30	V
Gate –Source Voltage		V_{GSS}	±12	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	-0.45	A
	T_A=80℃		-0.35	
Pulsed Drain Current		I_{DM}	-1.0	A
Continuous Source Current(Diode Conduction)		I_S	-0.3	A
Power Dissipation	T_A=25℃	P_D	0.27	W
	T_A=70℃		0.16	
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃

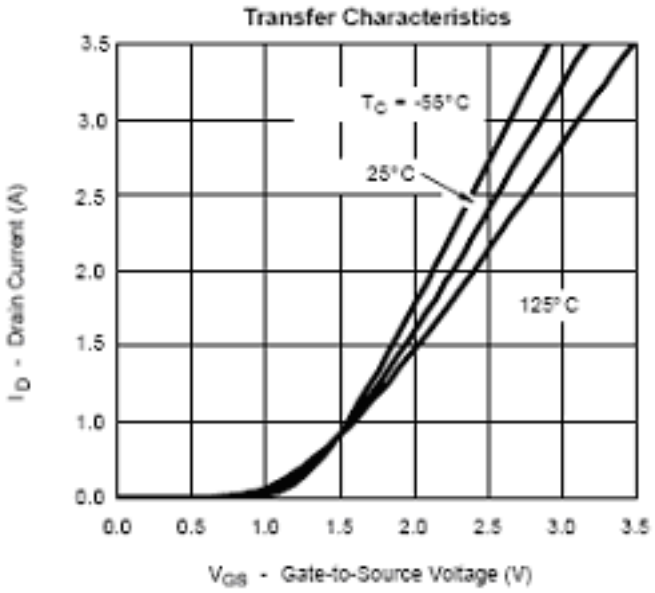
ELECTRICAL CHARACTERISTICS

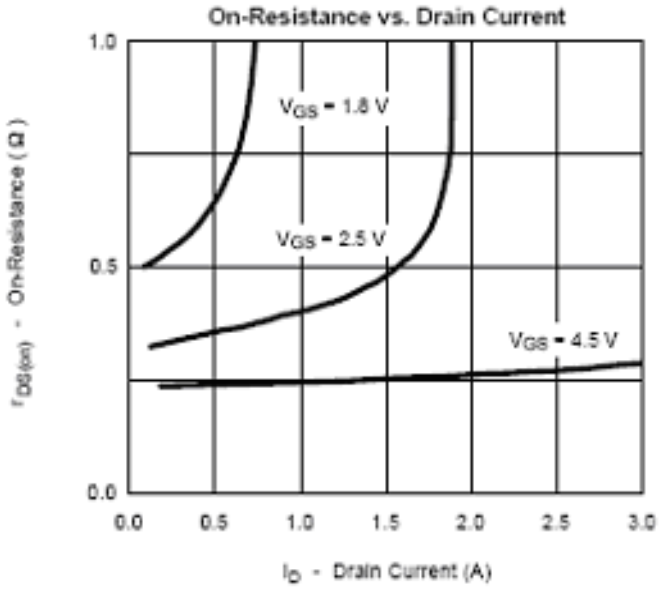
(T_A=25℃ Unless otherwise noted)

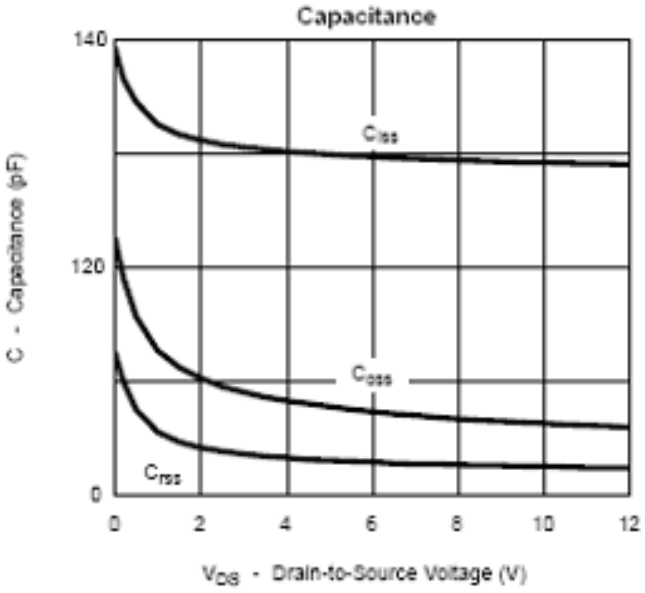
Parameter Symbol		Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-0.35		-1.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±30	uA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V,V_{GS}=0V			-1	uA
		V_{DS}=-24V,V_{GS}=0V T_J=55℃			-5	
On-State Drain Current	$I_{D(on)}$	V_{DS}≤ -4.5V,V_{GS} =-5V	-0.7			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-4.5V,I_D=-0.45A			0.65	Ω
		V_{GS}=-2.5V,I_D=-0.35A			0.90	
		V_{GS}=-1.8V,I_D=-0.25A			1.50	
Forward Transconductance	gfs	V_{DS}=-10V,I_D=-0.25A		0.4		S
Diode Forward Voltage	V_{SD}	I_S=-0.15A,V_{GS}=0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-10V,V_{GS}=-4.5V ,I_D ≡-0.6A	1.5		2.0	nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			0.35		
Turn-On Time	$t_{d(on)}$	V_{DD}=-10V,R_L=10Ω , I_D≡-0.4A V_{GEN}=-4.5V ,R_G=6Ω	5		10	ns
	t_r			15	25	
Turn-Off Time	$t_{d(off)}$			8	15	
	t_f			1.4	1.8	

TYPICAL CHA RACTERISTICS









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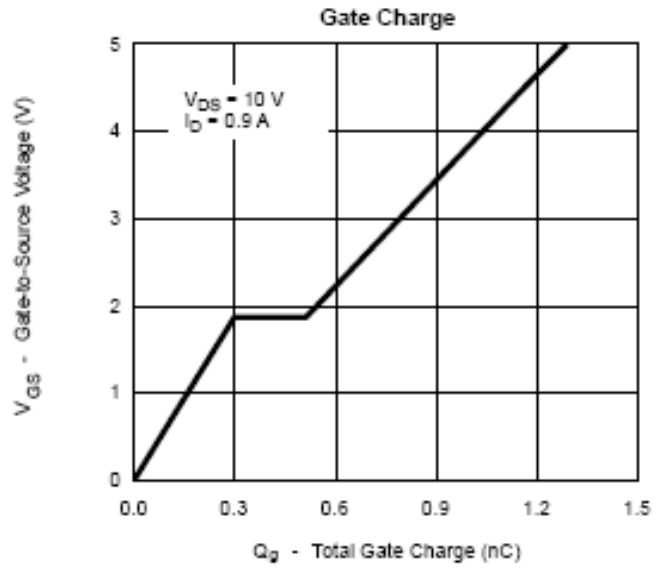

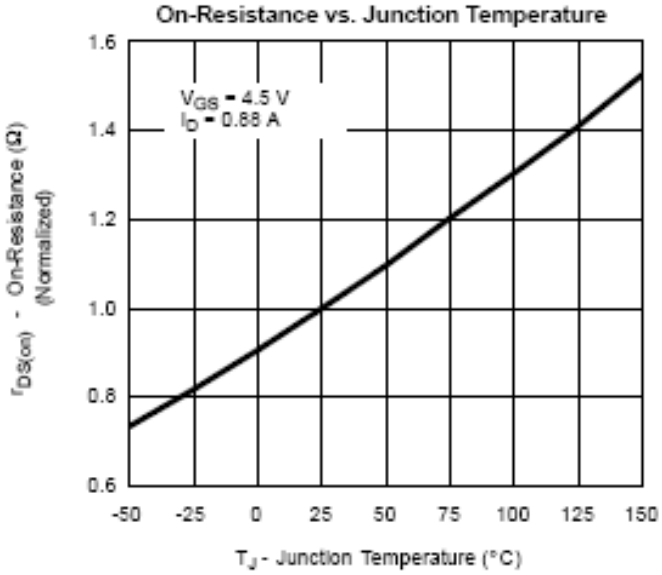

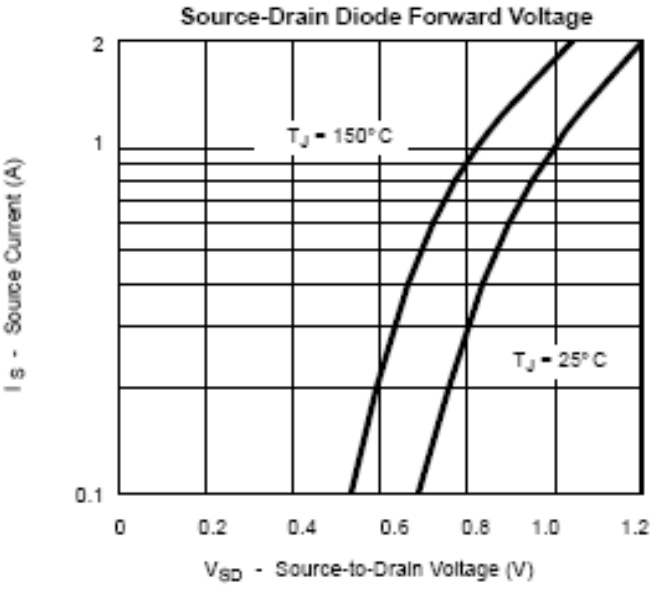

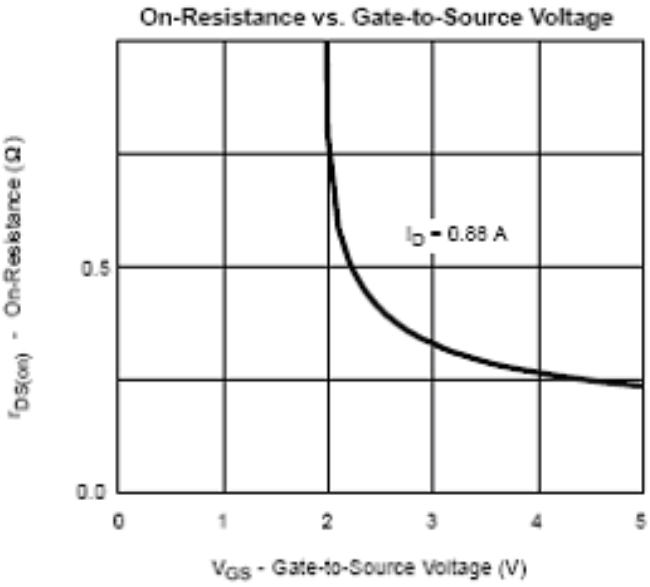

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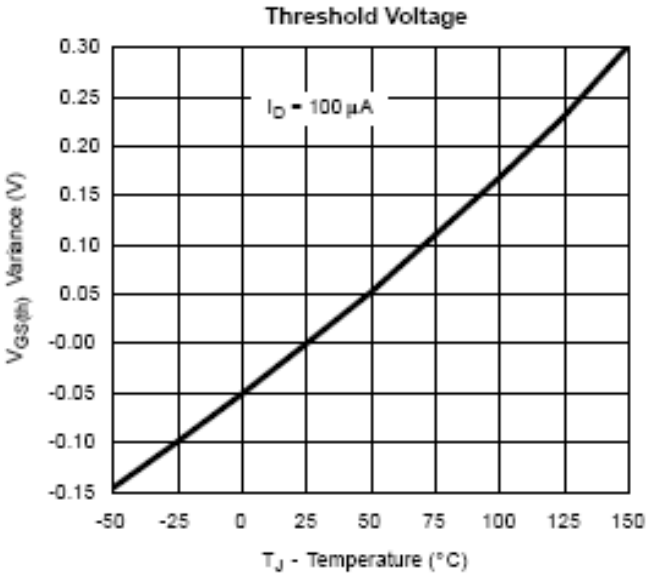
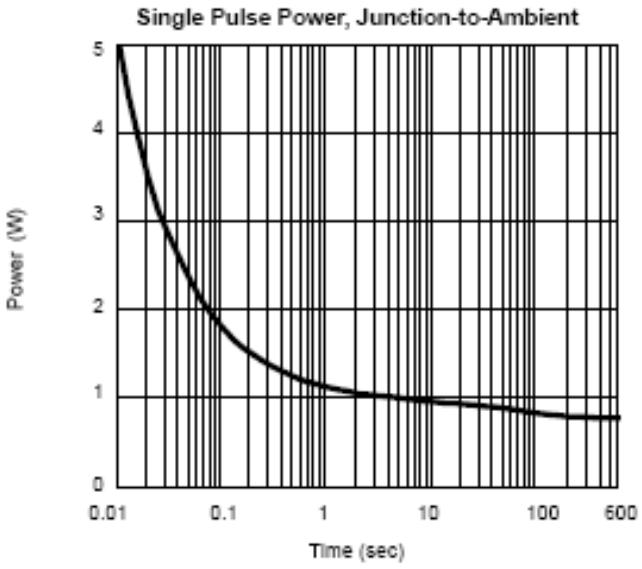
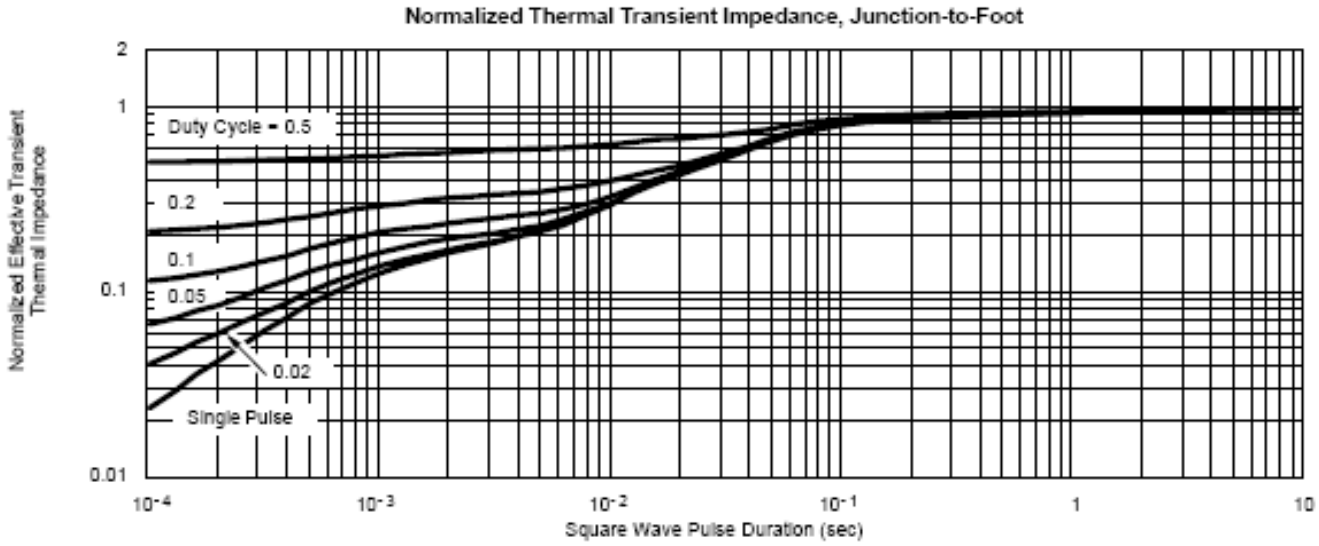
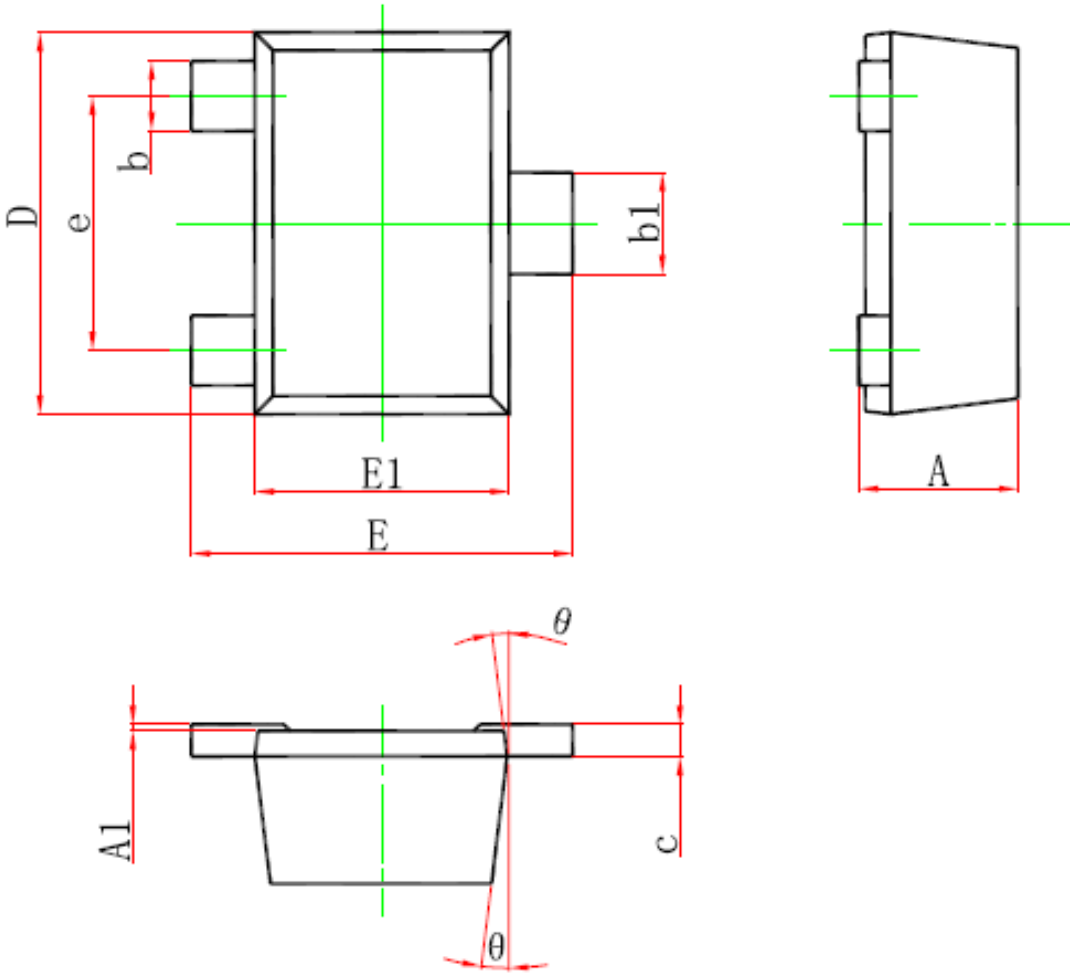






SOT-723 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		0.500		0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
c		0.150		0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
e	0.800TYP.		0.031TYP.	
θ	7° REF.		7° REF.	

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